## EAST Search History

| Ref<br># | Hits | Search Query  | DBs   | Default<br>Operator | Plurals | Time Stamp          |
|----------|------|---|---|---------------------|---------|---------------------|
| L1       | 139  | (substrate or carrier or base or plate) same (gate near electrode) and (gate near (insulat \$4 or dielectric or oxide)) same (gate near electrode) and (source same (gate near (insulat\$4 or dielectric or oxide))) and (drain same(gate near (insulat\$4 or dielectric or oxide))) and (organic near9 semiconductor) and passivat\$4 and parylene     | US-PGPUB;<br>USPAT;<br>USOCR; FPRS;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR                  | ON      | 2008/09/23<br>12:08 |
|          | 15   | (substrate or carrier or base or plate) same (gate near electrode) and (gate near (insulat \$4 or dielectric or oxide)) same (gate near electrode) and (source same (gate near (insulat \$4 or dielectric or oxide))) and (drain same(gate near (insulat \$4 or dielectric or oxide))) and (organic near9 semiconductor) and passivat \$4 same parylene | US-PGPUB;<br>USPAT;<br>USOCR; FPRS;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR                  | SOO     | 2008/09/23<br>12:09 |
| L3       | 14   | (substrate or carrier or base or plate) same (gate near electrode) and (gate near (insulat \$4 or dielectric or oxide)) same (gate near electrode) and (source same (gate near (insulat\$4 or dielectric or oxide))) and (drain same(gate near (insulat\$4 or dielectric or oxide))) and (organic near9   | US-PGPUB;<br>USPAT;<br>USOCR; FPRS;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR                  |         | 2008/09/23<br>12:09 |

|    |      | semiconductor) and passivat\$4 same parylene and transistor  |   | *************************************** |    |                     |
|----|------|--|---|---|----|---------------------|
| L4 | 4504 | (organic near<br>semiconductor) near<br>(film or layer)  | US-PGPUB;<br>USPAT;<br>USOCR; FPRS;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR                                      | ON | 2008/09/23<br>13:02 |
| L5 | 1285 | (organic near<br>semiconductor) near<br>(film or layer) same<br>(gate near (insulat\$4<br>or oxide or dielectric))                                     | US-PGPUB;<br>USPAT;<br>USOCR; FPRS;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR                                      | ON | 2008/09/23<br>13:03 |
| L6 | 1101 | (organic near<br>semiconductor) near<br>(film or layer) same<br>(gate near (insulat\$4<br>or oxide or dielectric))<br>same source                      | US-PGPUB;<br>USPAT;<br>USOCR; FPRS;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR                                      | ON | 2008/09/23<br>13:03 |
| L7 | 1097 | (organic near<br>semiconductor) near<br>(film or layer) same<br>(gate near (insulat\$4<br>or oxide or dielectric))<br>same source same<br>drain        | US-PGPUB;<br>USPAT;<br>USOCR; FPRS;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR                                      | ON | 2008/09/23<br>13:03 |
| L8 | 1020 | (organic near semiconductor) near (film or layer) same (gate near (insulat\$4 or oxide or dielectric)) same source same drain and transistor           | US-PGPUB;<br>USPAT;<br>USOCR; FPRS;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR                                      | ON | 2008/09/23<br>13:03 |
| L9 | 139  | (organic near semiconductor) near (film or layer) same (gate near (insulat\$4 or oxide or dielectric)) same source same drain and transistor and array | US-PGPUB;<br>USPAT;<br>USOCR; FPRS;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR                                      | ON | 2008/09/23<br>13:03 |

| L10 | 117 | (organic near semiconductor) near (film or layer) same (gate near (insulat\$4 or oxide or dielectric)) same source same drain and transistor and array and (hole or via or trench or opening or recess or aperture or groove)              | US-PGPUB;<br>USPAT;<br>USOCR; FPRS;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON | 2008/09/23<br>13:04 |
|-----|-----|--|---|----|----|---------------------|
| L11 | 24  | (organic near semiconductor) near (film or layer) same (gate near (insulat\$4 or oxide or dielectric)) same source same drain and transistor and array and (hole or via or trench or opening or recess or aperture or groove) and parylene | US-PGPUB;<br>USPAT;<br>USOCR; FPRS;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON | 2008/09/23<br>13:05 |
| L12 | 400 | transistor and (pixel<br>near electrode) same<br>(organic near<br>semiconductor)   | US-PGPUB;<br>USPAT;<br>USOCR; FPRS;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON | 2008/09/23<br>13:16 |
| L13 | 55  | transistor and (pixel<br>near electrode) same<br>(organic near<br>semiconductor) and<br>(array near panel)   | US-PGPUB;<br>USPAT;<br>USOCR; FPRS;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON | 2008/09/23<br>13:16 |
| L14 | 45  | transistor and (pixel near electrode) same (organic near semiconductor) and (array near panel) and (contact near hole)   | US-PGPUB;<br>USPAT;<br>USOCR; FPRS;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON | 2008/09/23<br>13:17 |
| L15 | 43  | transistor and (pixel near electrode) same (organic near semiconductor) and (array near panel) and (contact near hole) and (drain near electrode)  | US-PGPUB;<br>USPAT;<br>USOCR; FPRS;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON | 2008/09/23<br>13:17 |

| L16 | 43    | transistor and (pixel near electrode) same (organic near semiconductor) and (array near panel) and (contact near hole) and (drain near electrode) and (gate near (insulat\$4 or oxide or dielectric)) | US-PGPUB;<br>USPAT;<br>USOCR; FPRS;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON | 2008/09/23<br>13:18 |
|-----|-------|---|---|----|----|---------------------|
| L17 | 27657 | (pixel near electrode)<br>same transistor   | US-PGPUB;<br>USPAT;<br>USOCR; FPRS;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON | 2008/09/23<br>13:20 |
| L18 | 197   | (pixel near electrode)<br>same transistor same<br>(organic near<br>semiconductor)   | US-PGPUB;<br>USPAT;<br>USOCR; FPRS;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON | 2008/09/23<br>13:20 |
| L19 | 34    | (pixel near electrode) same transistor same (organic near semiconductor) and parylene   | US-PGPUB;<br>USPAT;<br>USOCR; FPRS;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON | 2008/09/23<br>13:20 |

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